

## Erratum: “Pressure dependence of SiO<sub>2</sub> growth kinetics and electrical properties on SiC” [J. Appl. Phys. 103, 023522 (2008)]

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The horizontal axis in Fig. 6 was labeled incorrectly. The revised figure is depicted below. Note that it does not affect the conclusions made in the manuscript.

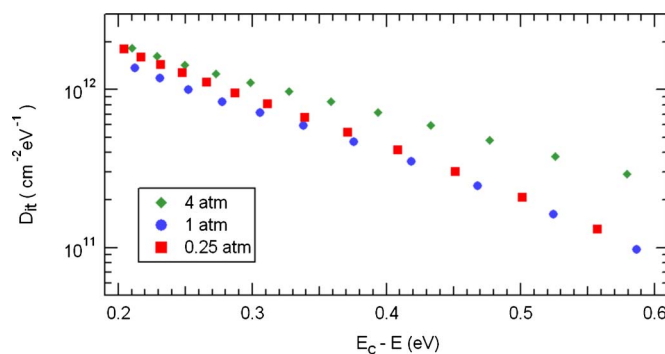


FIG. 6. (Color online) Measured interface trap densities in the upper part of the 4H-SiC band gap for oxides grown at 0.25, 1, and 4 atm on the (0001) Si-terminated face.

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